



PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (MMBT5551)
- Ideal for Low Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 2 and 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Device Schematic



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	Ic	-600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead. Halogen and Antimony Free.

 3. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160	_	V	$I_C = -100 \mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150	_	V	$I_C = -1.0 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	_	V	$I_E = -10\mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}	_	-50	nA μA	$V_{CB} = -120V, I_{E} = 0$ $V_{CB} = -120V, I_{E} = 0, T_{A} = 100^{\circ}C$		
Emitter Cutoff Current	I _{EBO}	_	-50	nA	V _{EB} = -3.0V, I _C = 0		
ON CHARACTERISTICS (Note 4)	230		l.		, 0		
		50	_		$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$		
DC Current Gain	h _{FE}	60	240	_	$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$		
		50	—		$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$		
Collector Emitter Seturation Voltage	V _{CE(SAT)}	_	-0.2 -0.5	V	$I_C = -10mA$, $I_B = -1.0mA$		
Collector-Emitter Saturation Voltage					$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-1.0	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$		
Ů					$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}	_	6.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$		
Small Signal Current Gain	h _{fe}	40	200	_	$V_{CE} = -10V$, $I_{C} = -1.0mA$, $f = 1.0kHz$		
Current Gain-Bandwidth Product	f _T	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz		
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5.0V$, $I_{C} = -200\mu A$, $R_{S} = 10\Omega$, $f = 1.0kHz$		

Notes: 4. Short duration pulse test used to minimize self-heating effect.

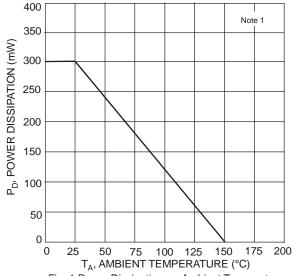


Fig. 1 Power Dissipation vs. Ambient Temperature

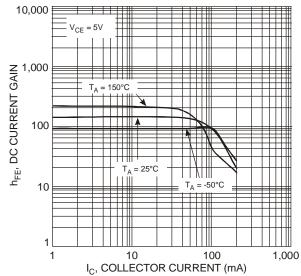
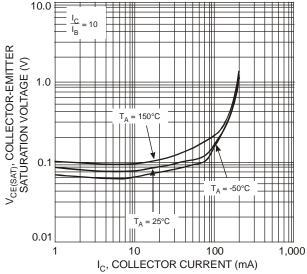


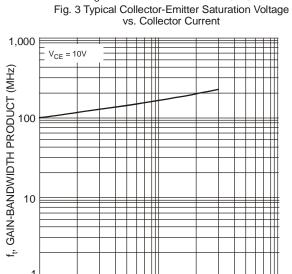
Fig. 2 Typical DC Current Gain vs. Collector Current

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 $\rm I_{\rm C}$, COLLECTOR CURRENT (mA) Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current

1.0 BASE-EMITTER TURN-ON VOLTAGE (V) 0.9 T_A = -50°C 0.8 0.7 0.6 0.5 0.4 $T_A = 150^{\circ}C$ 0.3 V_{BE(ON)}, E 0.2 0.1 0.1 10 I_C, COLLECTOR CURRENT (mA)

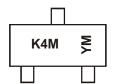
Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

Ordering Information (Note 5)

	Part Number	Case	Packaging
ı	MMBT5401-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



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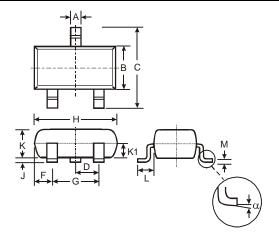
K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002)M = Month (ex: 9 = September)

Date Code Kev

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	M	N	Р	R	S	Т	U	V	W	Χ	Υ	Z	Α	В	С
Month	Jan	1	Feb	Mai	·	Apr	May	у	Jun	Jul		Aug	Sep)	Oct	Nov	,	Dec
Code	1		2	3		4	5		6	7		8	9		0	N		D

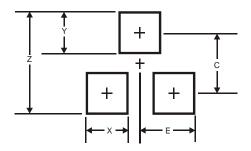


Package Outline Dimensions



	SOT-23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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